

ABSTRACT

An object of the present invention is to provide an optimum ceramic substrate being excellent in temperature rising property and breakdown voltage and Young's modulus at a high temperature as a substrate for producing/examining a semiconductor, and in the ceramic substrate of the present invention having a conductor on a surface or inside thereof, the ceramic substrate has a leakage quantity of 10^{-7} Pa · m³ / sec (He) or less by measurement with a helium leakage detector.

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